

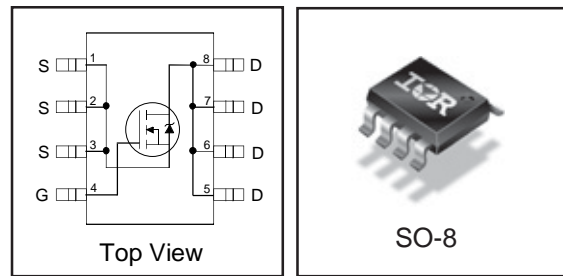
**Applications**

- High frequency DC-DC converters
- Lead-Free

<b>V<sub>DSS</sub></b>	<b>R<sub>DS(on)</sub> max</b>	<b>I<sub>D</sub></b>
<b>200V</b>	<b>0.73Ω</b>	<b>1.2A</b>

**Benefits**

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C<sub>OSS</sub> to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

	Parameter	Max.	Units
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	1.2	A
I <sub>D</sub> @ T <sub>A</sub> = 70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	1.0	
I <sub>DM</sub>	Pulsed Drain Current ①	10	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
V <sub>GS</sub>	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ②	6.8	V/ns
T <sub>J</sub>	Operating Junction and	-55 to + 150	°C
T <sub>STG</sub>	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Typical SMPS Topologies**

- Telecom 48V input Forward Converter

# IRF7464PbF

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Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	200	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.23	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.73	$\Omega$	$V_{GS} = 10V, I_D = 0.72A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 200V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 160V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	1.1	—	—	S	$V_{DS} = 50V, I_D = 0.72A$
$Q_g$	Total Gate Charge	—	9.5	14	nC	$I_D = 0.72A$
$Q_{gs}$	Gate-to-Source Charge	—	2.5	3.8		$V_{DS} = 160V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	4.6	6.9		$V_{GS} = 10V, \text{④}$
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = 100V$
$t_r$	Rise Time	—	9.5	—		$I_D = 0.72A$
$t_{d(off)}$	Turn-Off Delay Time	—	18	—		$R_G = 24\Omega$
$t_f$	Fall Time	—	15	—		$V_{GS} = 10V, \text{④}$
$C_{iss}$	Input Capacitance	—	280	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	52	—		$V_{DS} = 25V$
$C_{rSS}$	Reverse Transfer Capacitance	—	14	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	330	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	25	—		$V_{GS} = 0V, V_{DS} = 160V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	48	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 160V \text{ ⑥}$

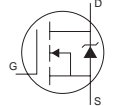
## Avalanche Characteristics

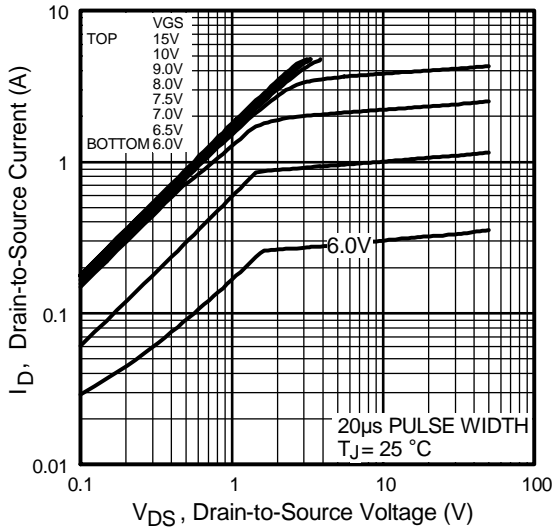
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	68	mJ
$I_{AR}$	Avalanche Current①	—	1.2	A
$E_{AR}$	Repetitive Avalanche Energy①	—	0.25	mJ

## Thermal Resistance

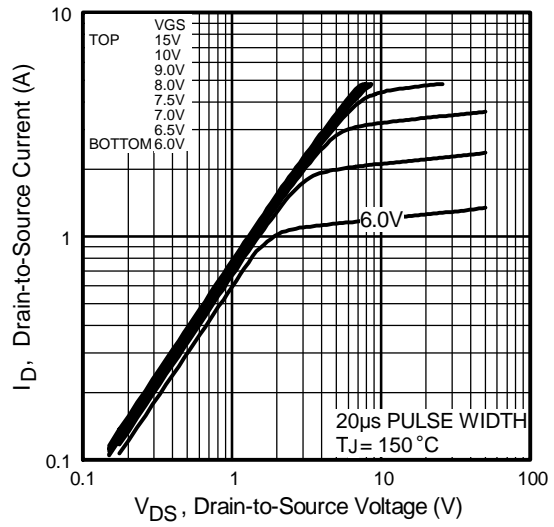
	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient⑥	—	50	°C/W

## Diode Characteristics

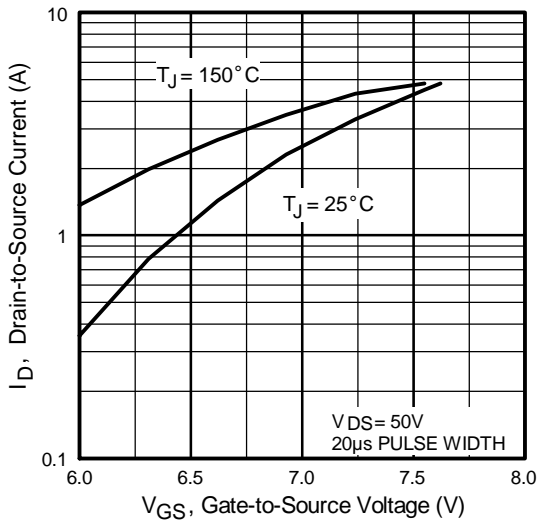
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	10		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 0.72A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	60	90	ns	$T_J = 25^\circ\text{C}, I_F = 0.72A$
$Q_{rr}$	Reverse Recovery Charge	—	130	200	nC	$di/dt = 100A/\mu s$ ④



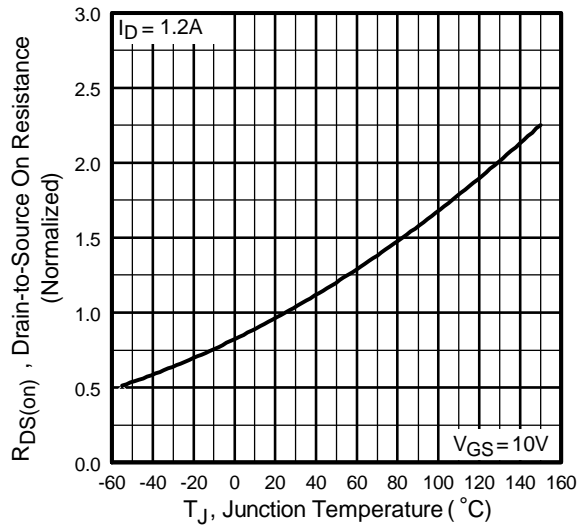
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics



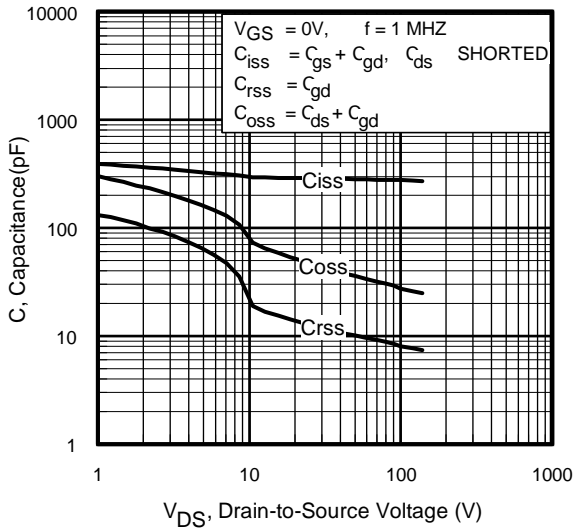
**Fig 3.** Typical Transfer Characteristics



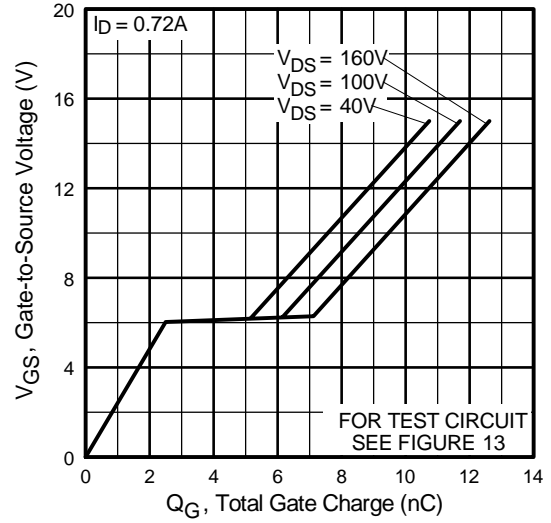
**Fig 4.** Normalized On-Resistance Vs. Temperature

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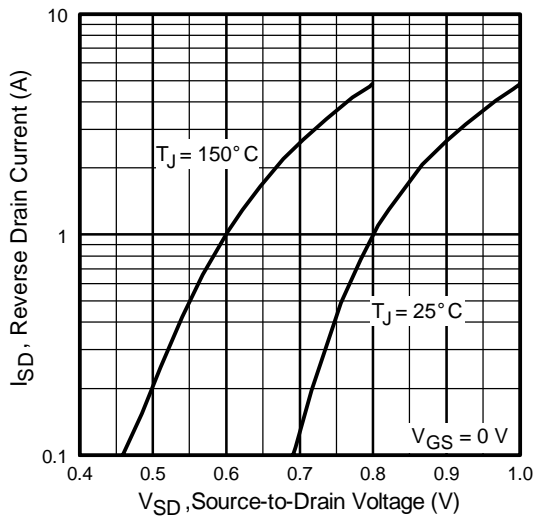
International  
**IR** Rectifier



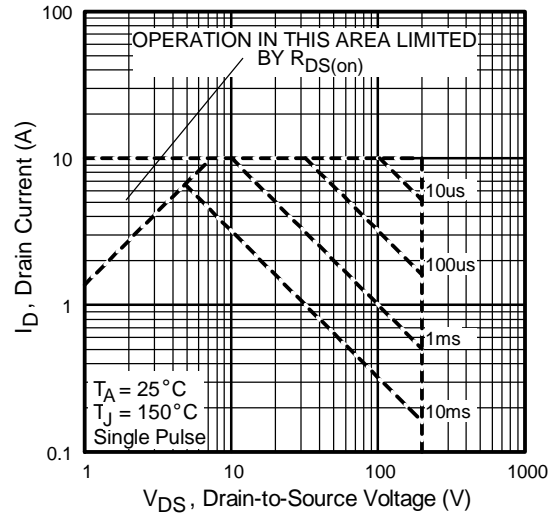
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



**Fig 7.** Typical Source-Drain Diode Forward Voltage

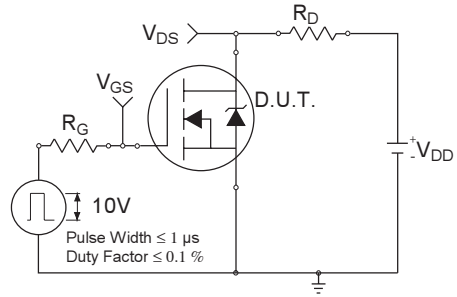
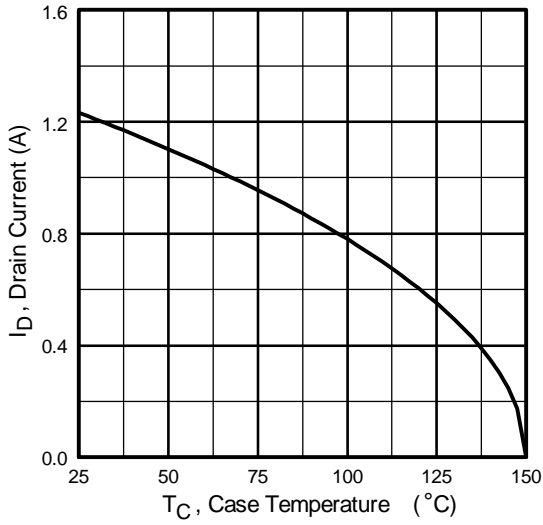


**Fig 8.** Maximum Safe Operating Area

**Fig 6. On-Resistance Vs. Drain Current**

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**IR** Rectifier

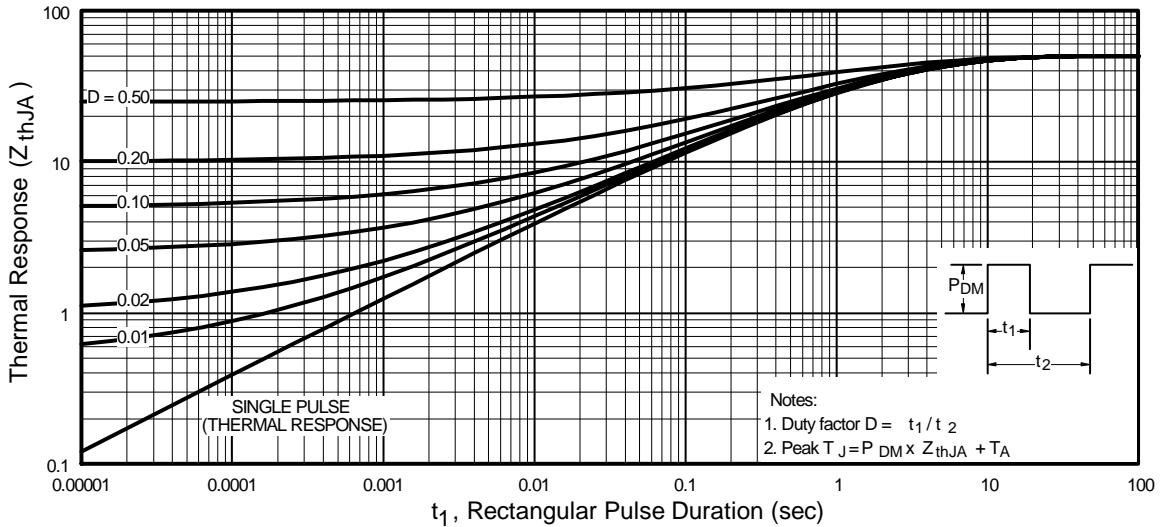
**IRF7464PbF**



**Fig 10a. Switching Time Test Circuit**



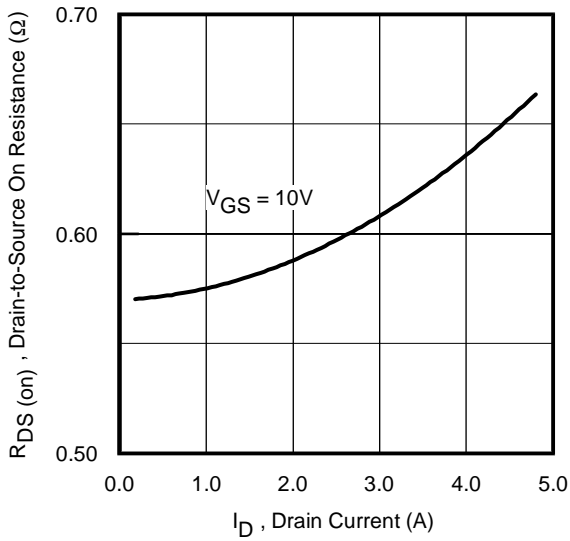
**Fig 10b. Switching Time Waveforms**



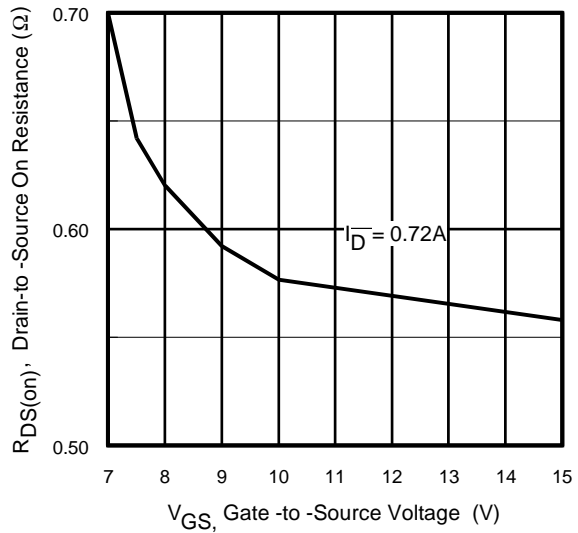
**Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient**

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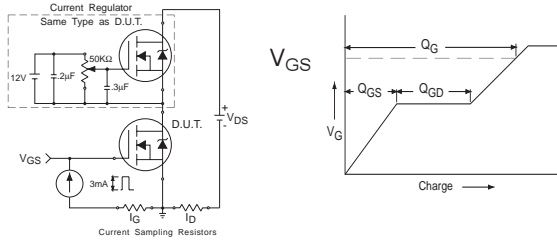
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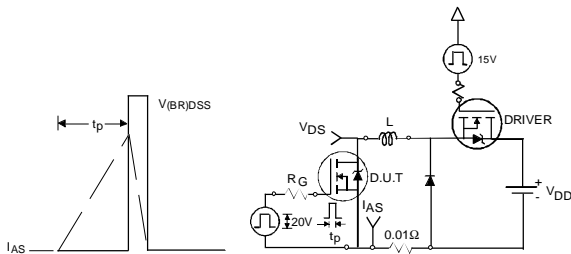
**Fig 12.** On-Resistance Vs. Drain Current



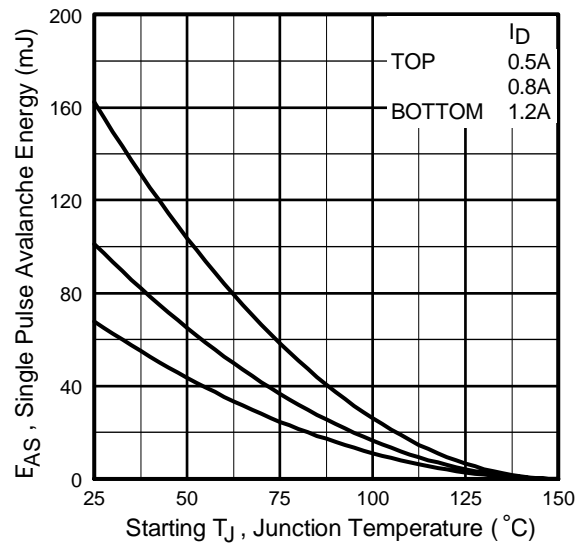
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 13a&b.** Basic Gate Charge Test Circuit and Waveform

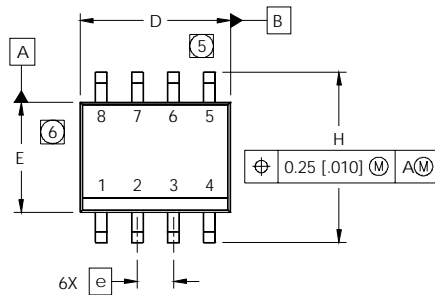


**Fig 14a&b.** Unclamped Inductive Test circuit and Waveforms

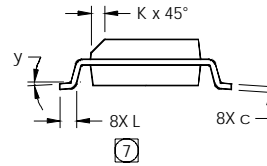
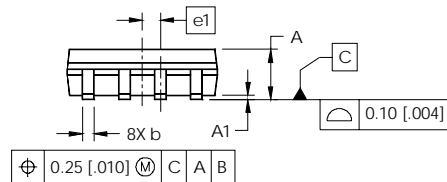


**Fig 14c.** Maximum Avalanche Energy Vs. Drain Current

## SO-8 Package Outline



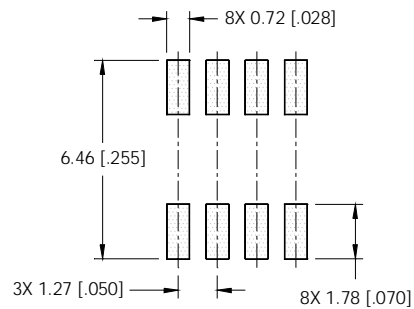
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



**NOTES:**

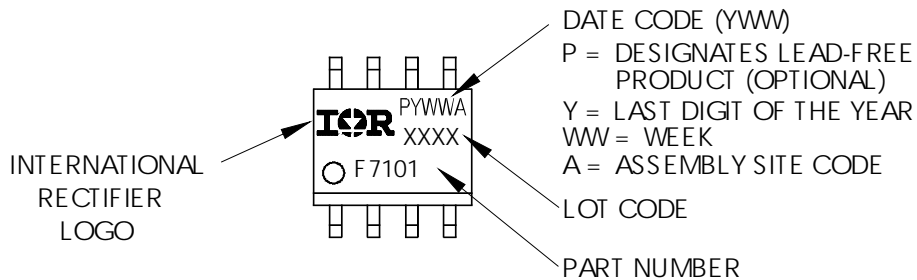
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [0.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [0.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

**FOOT PRINT**



## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

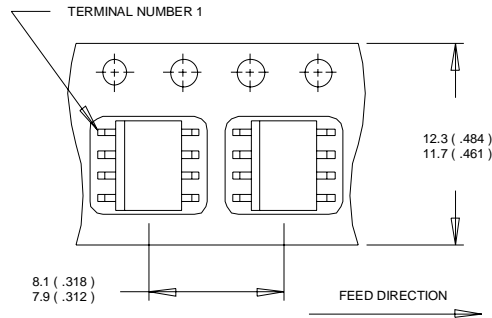


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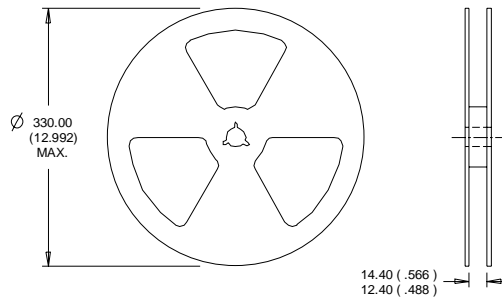
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)

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- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 94\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 1.2\text{A}$ .
- ③  $I_{SD} \leq 0.72\text{A}$ ,  $di/dt \leq 130\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 150^\circ\text{C}$
- ④ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{OSS}$  eff. is a fixed capacitance that gives the same charging time as  $C_{OSS}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$
- ⑥ When mounted on 1 inch square copper board,  $t < 10$  sec

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

International  
**IR** Rectifier

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